

HIGH EFFICIENCY FAST RECOVERY DIODES

MAIN PRODUCT CHARACTERISTICS

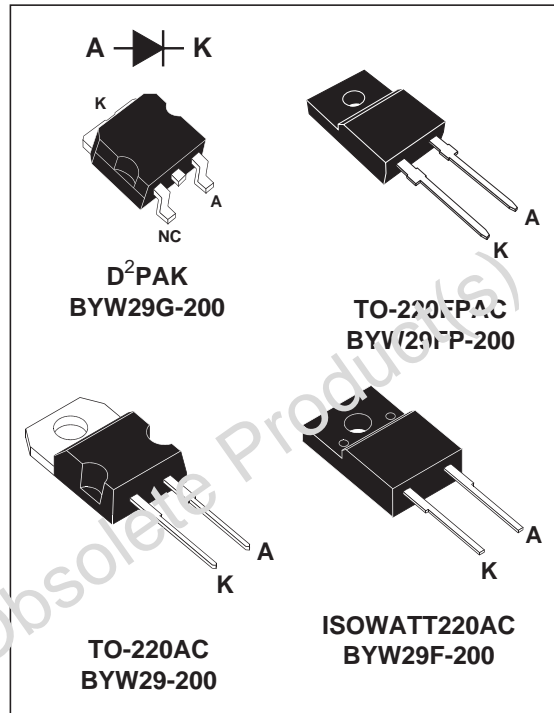
| | |
|-------------|--------|
| $I_{F(AV)}$ | 8 A |
| V_{RRM} | 200 V |
| trr (max) | 25 ns |
| V_F (max) | 0.85 V |

FEATURES AND BENEFITS

- Very Low Forward Losses
- Negligible switching losses
- High surge current capability
- Insulated packages (ISOWATT220AC, TO-220FPAC):
Insulation voltage: 2000 VDC
Typical insulation capacitance = 12 pF

DESCRIPTION

Single rectifier suited for Switch Mode Power Supply and high frequency DC to DC converters. Packaged in TO-220AC, ISOWATT220AC, TO-220FPAC and D²PAK, this device is intended for use in high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | | Value | Unit | |
|--------------|--|-------------------------------|---------------------------|------|---|
| V_{RRM} | Repetitive peak reverse voltage | | 200 | V | |
| $I_{F(RMS)}$ | RMS forward current | | 16 | A | |
| $I_{F(AV)}$ | Average forward current $\delta = 0.5$ | D ² PAK / TO-220AC | $T_c = 120^\circ\text{C}$ | 8 | A |
| | | ISOWATT220AC / TO-220FPAC | $T_c = 100^\circ\text{C}$ | | |
| I_{FSM} | Surge non repetitive forward current (All pins connected) | tp=10ms sinusoidal | 80 | A | |
| Tstg | Storage and junction temperature range | | - 65 to + 150 | °C | |
| Tj | Maximum operating junction temperature | | + 150 | | |

BYW29/F/FP/G-200**THERMAL RESISTANCE**

| Symbol | Parameter | | Value | Unit |
|-----------|-------------------------------------|-------------------|-------|------|
| Rth (j-c) | Junction to case thermal resistance | TO-220AC D2PAK | 2.8 | °C/W |
| | | ISOWATT220AC | 5 | |
| | | TO-220FPAC | 5.5 | |

STATIC ELECTRICAL CHARACTERISTICS

| Symbol | Parameter | Test Conditions | | Min. | Typ. | Max. | Unit |
|-------------------|-------------------------|-----------------------------------|------------------------|------|------|------|------|
| I _R * | Reverse leakage current | V _R = V _{RRM} | T _j = 25°C | | | 10 | μA |
| | | | T _j = 100°C | | | 0.6 | mA |
| V _F ** | Forward voltage drop | I _F = 5 A | T _j = 125°C | | | 0.85 | V |
| | | I _F = 10 A | T _j = 125°C | | | 1.05 | |
| | | I _F = 10 A | T _j = 25°C | | | 1.15 | |

Pulse test : * tp = 5 ms, duty cycle < 2 %

** tp = 380 μs, duty cycle < 2 %

To evaluate the conduction losses use the following equation :

$$P = 0.65 \times I_{F(AV)} + 0.040 I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

| Symbol | Parameter | Test Conditions | | Min. | Typ. | Max. | Unit |
|-----------------|-----------------------|--|-----------------------|------|------|------|------|
| t _{rr} | Reverse recovery time | T _j = 25°C | I _F = 0.5A | | | 25 | ns |
| | | I _{rr} = 0.25 A | I _R = 1A | | | | |
| t _{rr} | Reverse recovery time | T _j = 25°C | I _F = 1A | | | 35 | ns |
| | | di _F /dt = -50A/μs | V _R = 30V | | | | |
| t _{fr} | Forward recovery time | T _j = 25°C | I _F = 1A | | 15 | | ns |
| | | di _F /dt = 100A/μs | | | | | |
| | | V _{FR} = 1.1 x V _F max | | | | | |
| V _{FP} | Peak forward voltage | T _j = 25°C | I _F = 1A | | | | V |
| | | di _F /dt = 100A/μs | | | 2 | | |

Fig.1 : Average forward power dissipation versus average forward current.

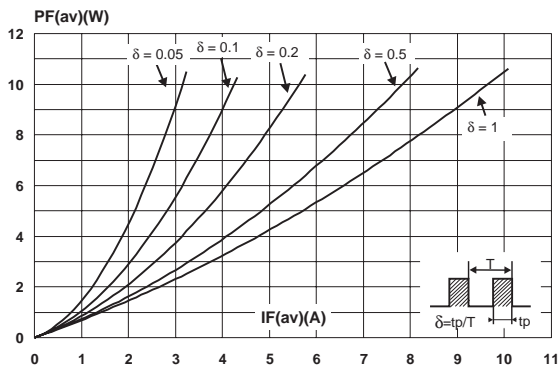


Fig.2 : Peak current versus form factor.

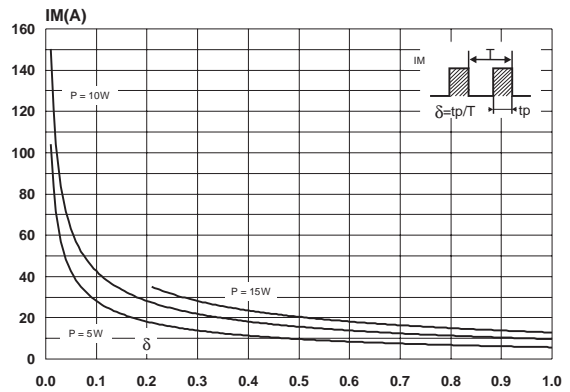


Fig.3 : Forward voltage drop versus forward current (maximum values).

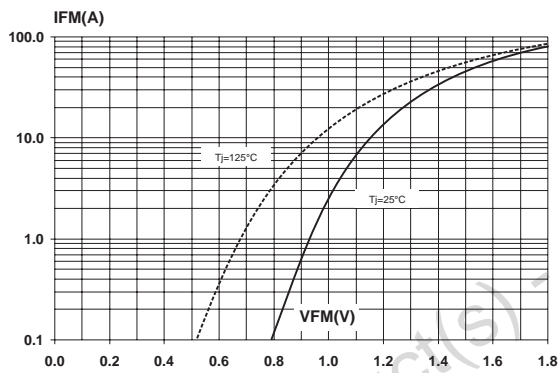


Fig.4-1 : Relative variation of thermal impedance junction to case versus pulse duration (TO-220AC, D²PAK).

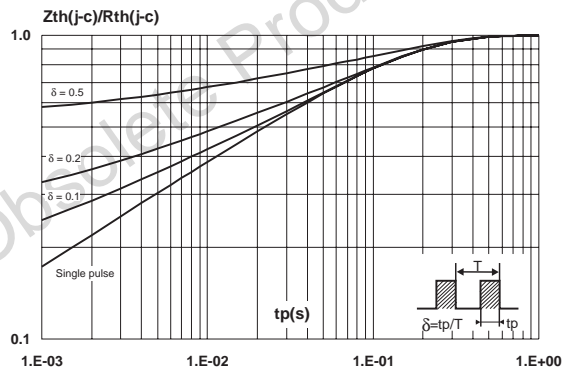


Fig.4-2 :Relative variation of thermal impedance junction to case versus pulse duration (TO-220FPAC, ISOWATT220AC).

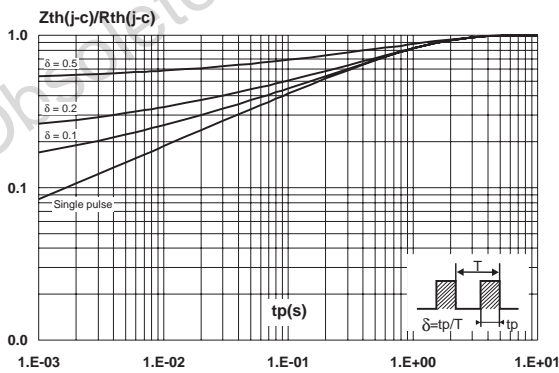


Fig.5-1 : Non repetitive surge peak forward current versus overload duration (TO-220AC, D²PAK).

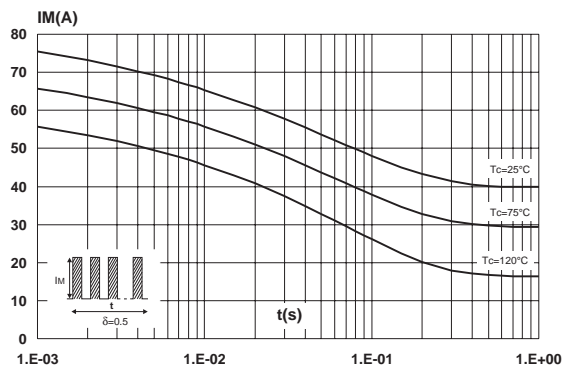


Fig.5-2 : Non repetitive surge peak forward current versus overload duration (TO-220FPAC, ISOWATT220AC).

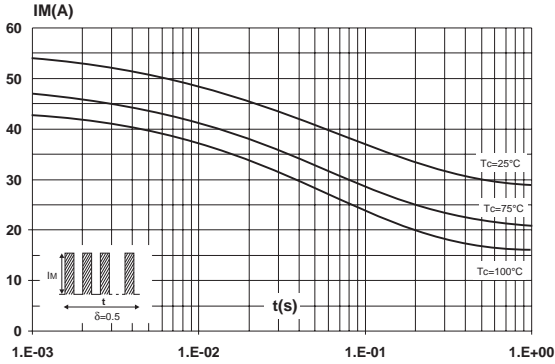


Fig.6 : Average current versus ambient temperature. ($\delta = 0.5$)

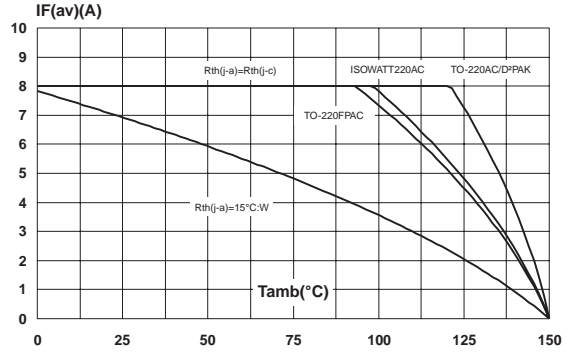


Fig.7 : Junction capacitance versus reverse voltage applied (Typical values).

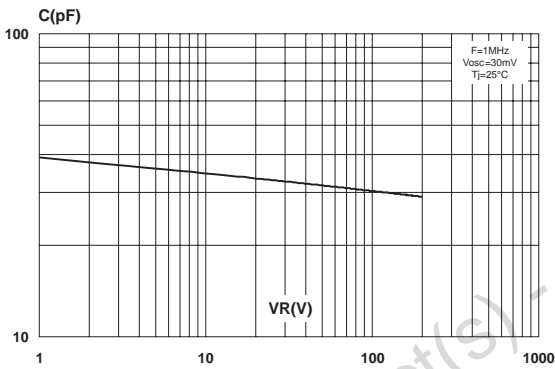


Fig.8 : Reverse recovery charges versus dI_F/dt (90% confidence).

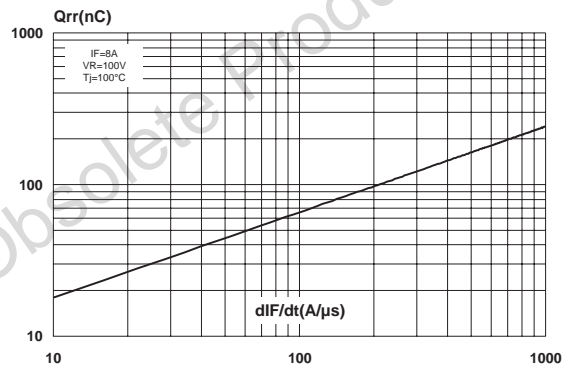


Fig.9 : Peak reverse recovery current versus dI_F/dt (90% confidence).

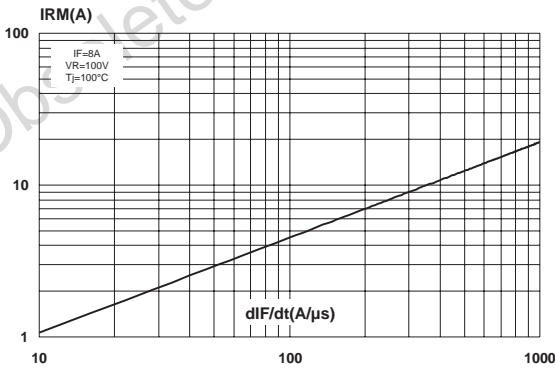


Fig.10 : Dynamic parameters versus junction temperature.

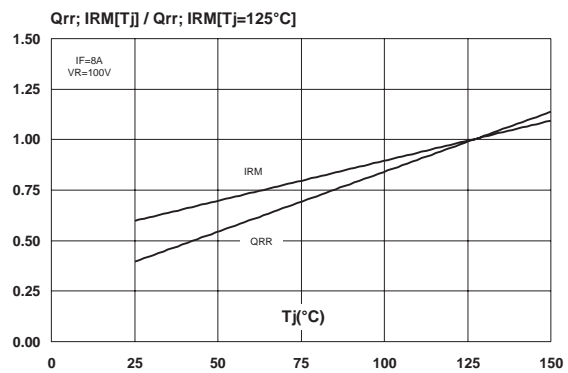
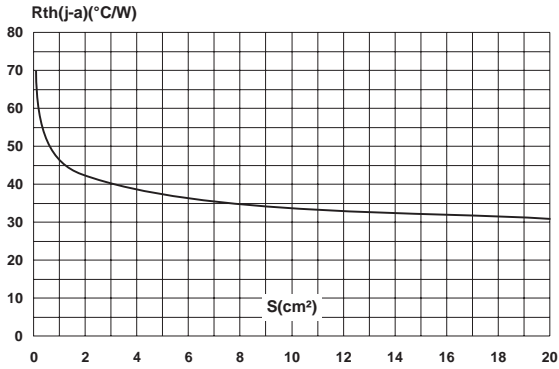
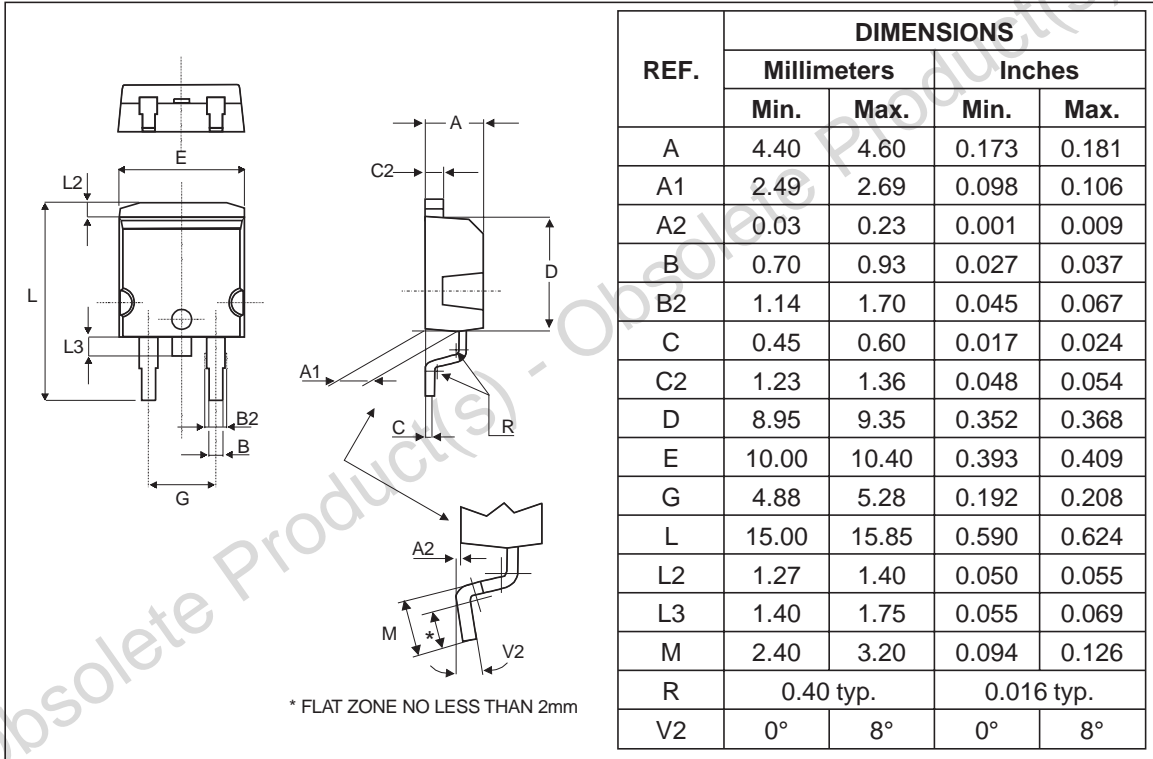


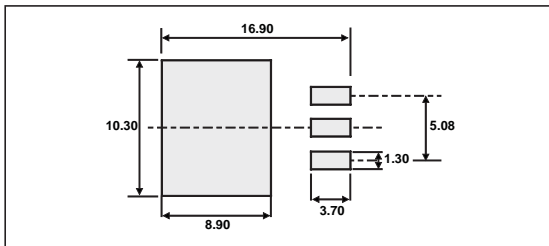
Fig.11 : Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35µm) for D²PAK.



PACKAGE MECHANICAL DATA
D²PAK (Plastic)

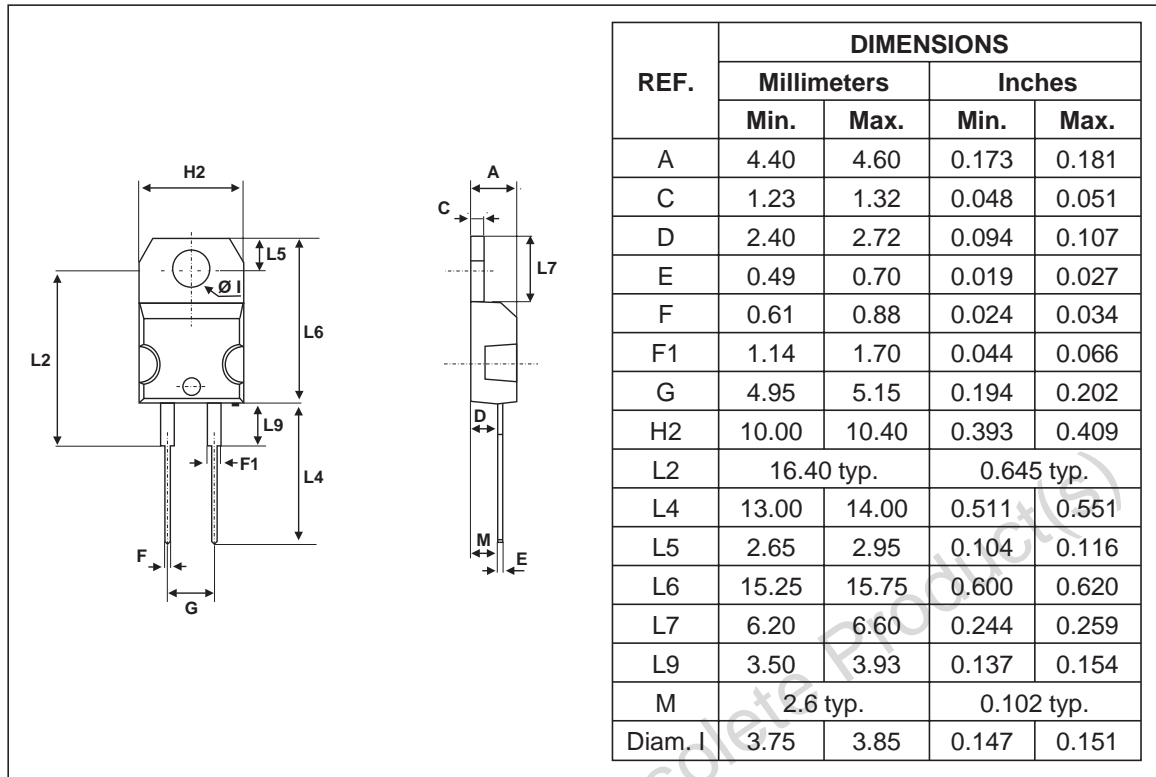


FOOT PRINT (in millimeters)

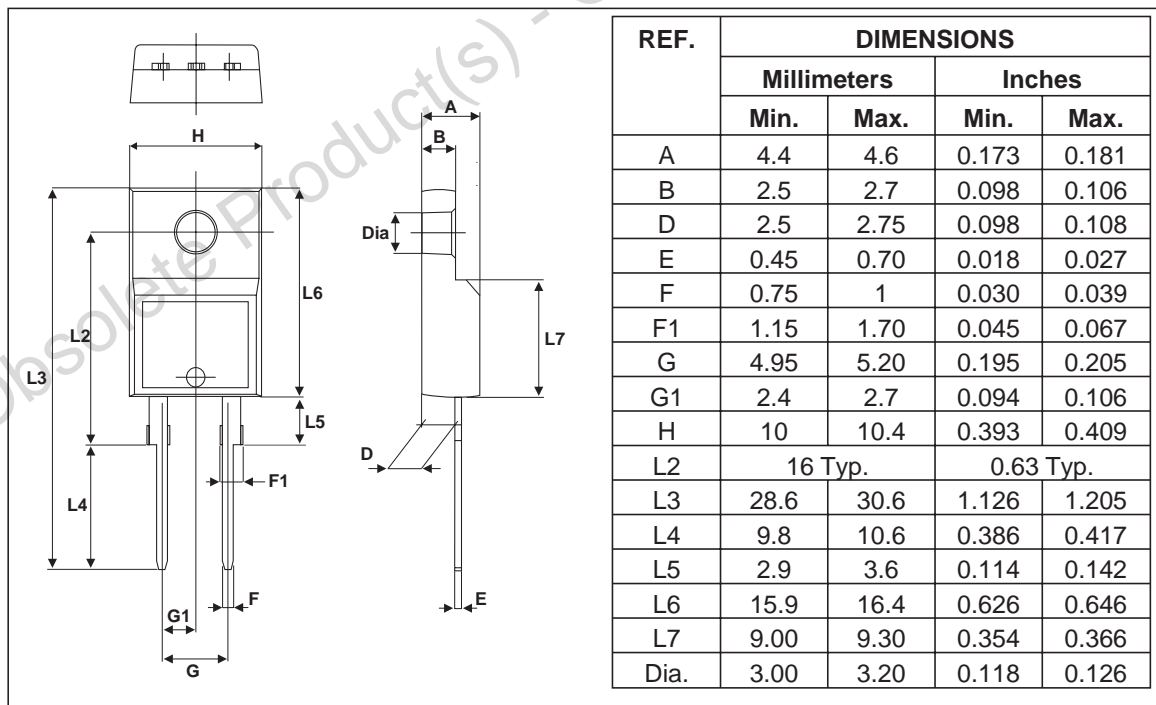


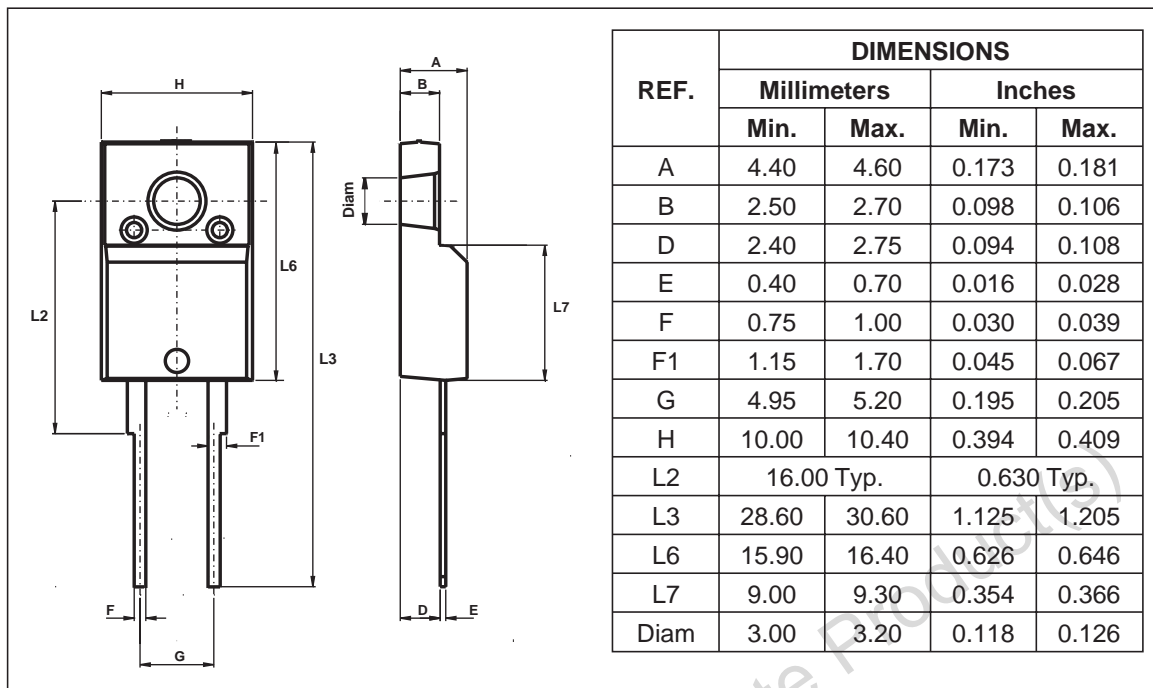
BYW29/F/FP/G-200

PACKAGE MECHANICAL DATA TO-220AC



PACKAGE MECHANICAL DATA TO-220FPAC



PACKAGE MECHANICAL DATA
 ISOWATT220AC


| Type | Marking | Package | Weight | Base Qty | Delivery Mode |
|-------------|-------------|--------------------|--------|----------|---------------|
| BYW29-200 | BYW29-200 | TO-220AC | 1.86 g | 50 | Tube |
| BYW29F-200 | BYW29F-200 | ISOWATT220AC | 2.2 g | 50 | Tube |
| BYW29FP-200 | BYW29FP-200 | TO-220FPAC | 2 g | 50 | Tube |
| BYW29G-200 | BYW29G-200 | D ² PAK | 1.48 g | 50 | Tube |

- Cooling method: by conduction (C)
- Recommended torque value (ISOWATT220AC, TO-220FPAC): 0.55 N.m
- Maximum torque value: 0.7 N.m
- Recommended torque value (TO-220AC): 0.8 N.m
- Maximum torque value: 1.0 N.m
- Epoxy meets UL94, V0

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